

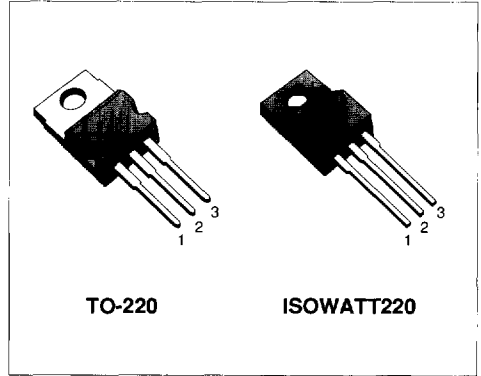
## N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STP3N90	900 V	4.5 Ω	3.2 A
STP3N90FI	900 V	4.5 Ω	1.9 A

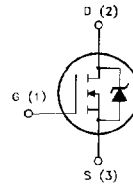
- AVALANCHE RUGGEDNESS TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INPUT CAPACITANCE
- LOW GATE CHARGE
- LOW LEAKAGE CURRENT SPECIFIED AT MAXIMUM VOLTAGE
- "DIPS" EDGE TERMINATION TO SUSTAIN HIGH VOLTAGE
- APPLICATION ORIENTED CHARACTERIZATION
- ISOLATED PACKAGE UL RECOGNIZED, ISOLATION TO 2000V DC

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CONSUMER AND INDUSTRIAL LIGHTING
- DC-AC INVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLY (UPS)



### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP3N90	STP3N90FI	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	900		V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	900		V
V <sub>GS</sub>	Gate-source Voltage	± 20		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	3.2	1.9	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	2	1.2	A
I <sub>DM</sub> (*)	Drain Current (pulsed)	13	13	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	100	40	W
	Derating Factor	0.8	0.32	W/°C
T <sub>stg</sub>	Storage Temperature	-65 to 150		°C
T <sub>J</sub>	Max. Operating Junction Temperature	150		°C

(\*) Pulse width limited by safe operating area

## THERMAL DATA

			TO-220	ISOWATT220	
$R_{th(j-case)}$	Thermal Resistance Junction-case	Max	1.25	3.12	°C/W
$R_{th(j-amb)}$	Thermal Resistance Junction-ambient	Max		62.5	°C/W
$R_{th(c-sink)}$	Thermal Resistance Case-sink	Typ		0.5	°C/W
$T_1$	Maximum Lead Temperature For Soldering Purpose			300	°C

## AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
$I_{AR}$	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by $T_j$ max, $\delta < 1\%$ )	3.2	A
$E_{AS}$	Single Pulse Avalanche Energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	160	mJ
$E_{AR}$	Repetitive Avalanche Energy (pulse width limited by $T_j$ max, $\delta < 1\%$ )	4.2	mJ
$I_{AR}$	Avalanche Current, Repetitive or Not-Repetitive ( $T_c = 100\text{ }^\circ\text{C}$ , pulse width limited by $T_j$ max, $\delta < 1\%$ )	2	A

ELECTRICAL CHARACTERISTICS ( $T_{case} = 25\text{ }^\circ\text{C}$  unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ $V_{GS} = 0$	900			V
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating} \times 0.8$ $T_c = 125\text{ }^\circ\text{C}$			250 1000	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body Leakage Current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{ V}$ $I_D = 1.7\text{ A}$ $V_{GS} = 10\text{ V}$ $I_D = 1.7\text{ A}$ $T_c = 100\text{ }^\circ\text{C}$			4.5 9	$\Omega$ $\Omega$
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10\text{ V}$	3.2			A

## DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 1.7\text{ A}$	1			S
$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$ $V_{GS} = 0$			850	pF
$C_{oss}$	Output Capacitance				105	pF
$C_{rss}$	Reverse Transfer Capacitance				40	pF

## ELECTRICAL CHARACTERISTICS (continued)

## SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Time Rise Time	$V_{DD} = 30\text{ V}$ $I_D = 2.1\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)			50 110	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 640\text{ V}$ $I_D = 3\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		170		A/ $\mu\text{s}$
$Q_g$	Total Gate Charge	$V_{DD} = 400\text{ V}$ $I_D = 3\text{ A}$ $V_{GS} = 10\text{ V}$		42	55	nC

## SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$	Off-voltage Rise Time	$V_{DD} = 640\text{ V}$ $I_D = 3\text{ A}$			120	ns
$t_f$	Fall Time	$R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)			25	ns
$t_c$	Cross-over Time				165	ns

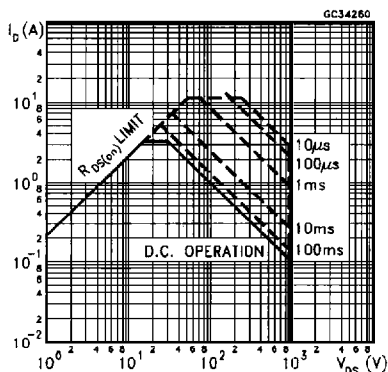
## SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}(\ast)$	Source-drain Current Source-drain Current (pulsed)				3.2 13	A A
$V_{SD}(\ast)$	Forward On Voltage	$I_{SD} = 3.2\text{ A}$ $V_{GS} = 0$			2	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 3\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 80\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		700		ns
$Q_{rr}$	Reverse Recovery Charge			8.8		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			25		A

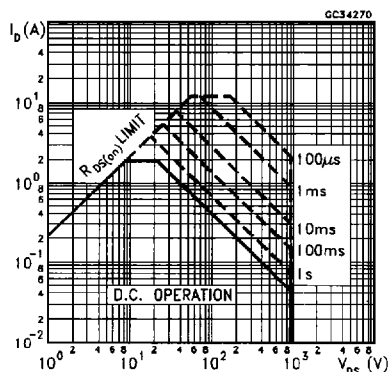
( $\ast$ ) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

( $\bullet$ ) Pulse width limited by safe operating area

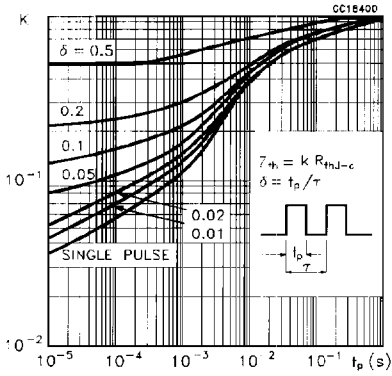
## Safe Operating Areas For TO220



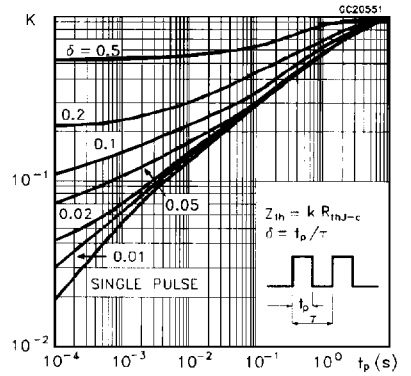
## Safe Operating Areas For ISOWATT220



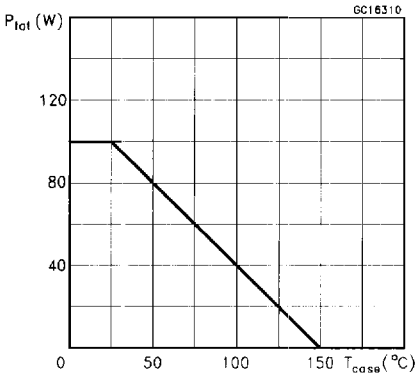
Thermal Impedance For TO-220



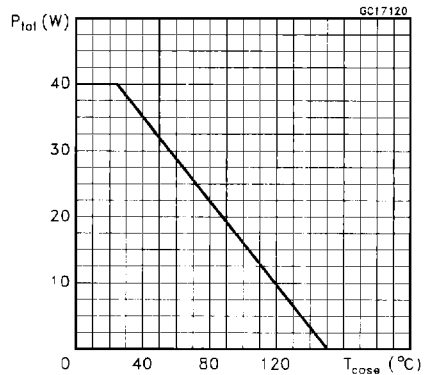
Thermal Impedance For ISOWATT220



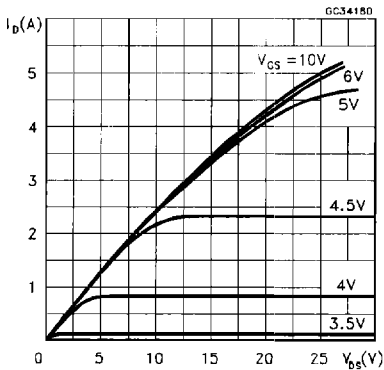
Derating Curve For TO-220



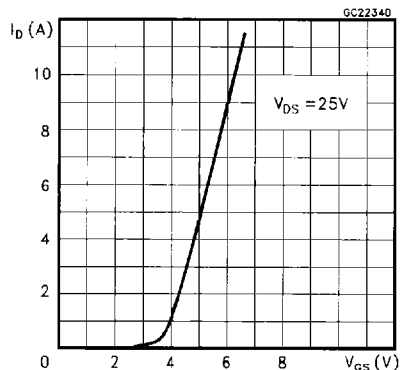
Derating Curve For ISOWATT220



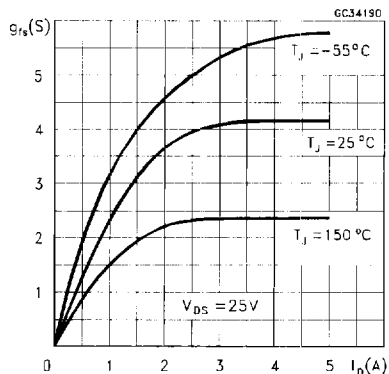
Output Characteristics



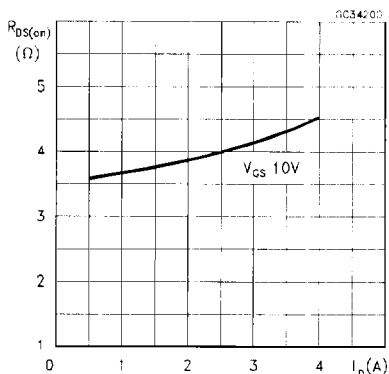
Transfer Characteristics



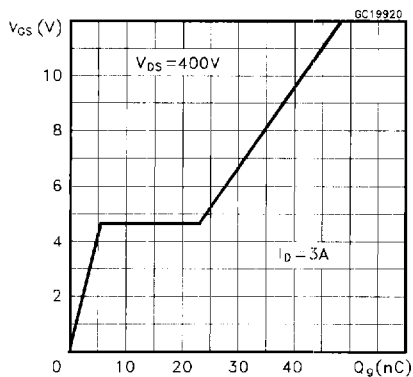
Transconductance



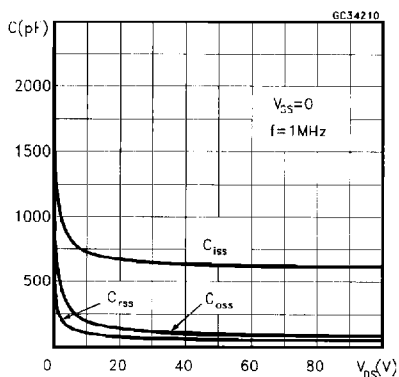
Static Drain-source On Resistance



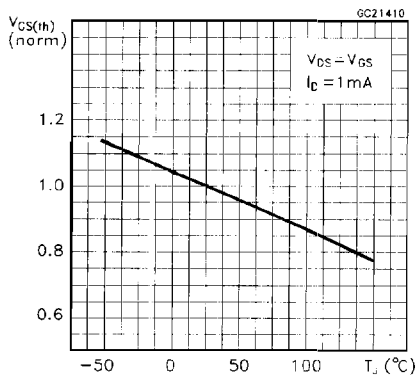
Gate Charge vs Gate-source Voltage



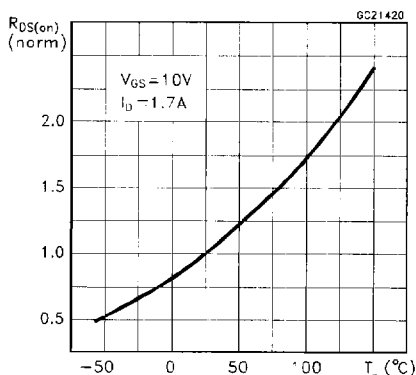
Capacitance Variations



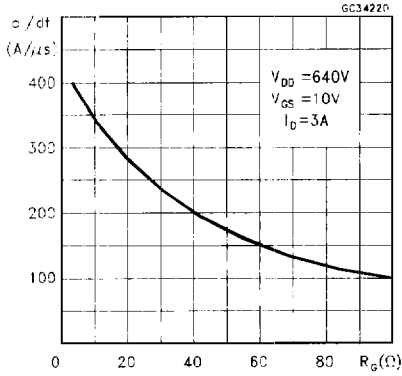
Normalized Gate Threshold Voltage vs Temperature



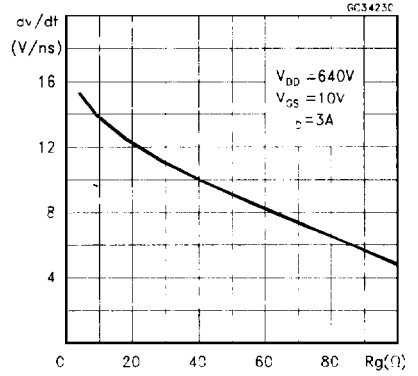
Normalized On Resistance vs Temperature



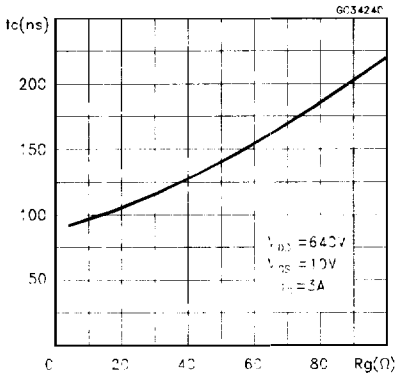
Turn-on Current Slope



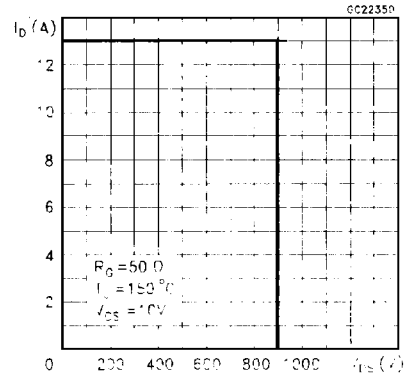
Turn-off Drain-source Voltage Slope



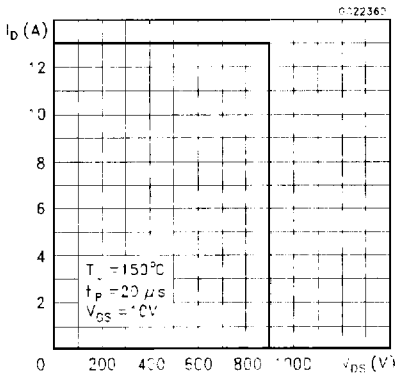
Cross-over Time



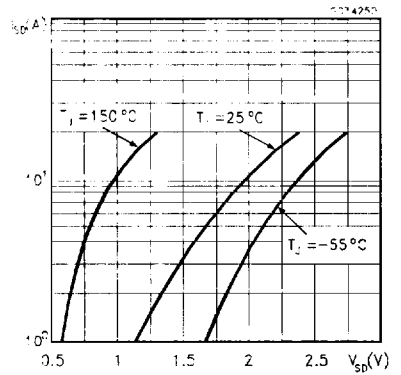
Switching Safe Operating Area



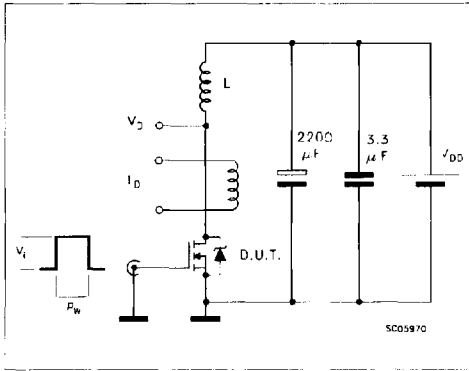
Accidental Overload Area



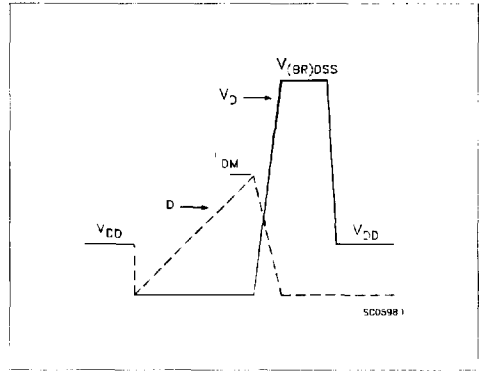
Source drain Diode Forward Characteristics



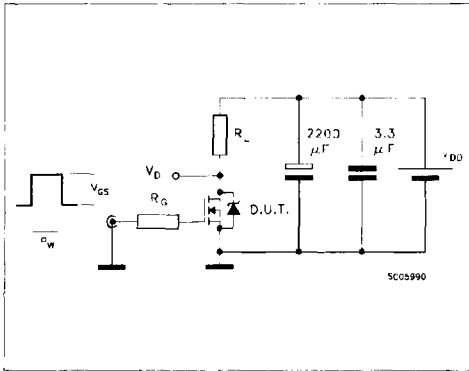
**Fig. 1: Unclamped Inductive Load Test Circuits**



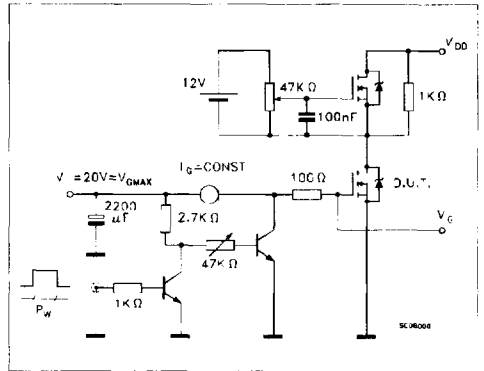
**Fig. 2: Unclamped Inductive Waveforms**



**Fig. 3: Switching Times Test Circuits For Resistive Load**



**Fig. 4: Gate Charge Test Circuit**



**Fig. 5: Test Circuit For Inductive Load Switching And Diode Reverse Recovery Time**

